

N-Channel Power MOSFET

600V, 0.55A, 15Ω

FEATURES

- Pb-free plating
- RoHS compliant
- Halogen-free

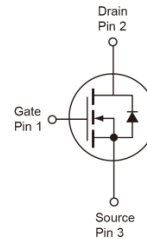
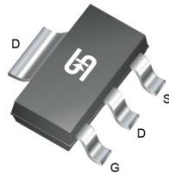
APPLICATIONS

- Lighting
- Charger
- Power Supply
- Switching applications

PRODUCT SUMMARY			
PARAMETER		VALUE	UNIT
V _{DS}		600	V
R _{DS(on)} (max)	V _{GS} = 10V	15	Ω
Q _g	V _{GS} = 10V	7.5	nC



SOT-223



Note: MSL 3 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	600	V
Gate-Source Voltage		V _{GS}	±30	V
Continuous Drain Current	T _C = 25°C	I _D	0.55	A
	T _C = 100°C		0.35	
	T _A = 25°C		0.23	
Pulsed Drain Current (Note 1)		I _{DM}	2.2	A
Total Power Dissipation	T _C = 25°C	P _D	10.4	W
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C

THERMAL RESISTANCE			
PARAMETER	SYMBOL	MAXIMUM	UNIT
Thermal Resistance – Junction to Case	R _{θJC}	12	°C/W
Thermal Resistance – Junction to Ambient (Note 2)	R _{θJA}	69	°C/W

Notes:

1. Pulsed width limited by maximum junction temperature pulse Width ≤ 100μs.
2. Device on a PCB FR4 with 1 in² (single layer, 2 oz thick) copper area for drain connection.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	BV_{DSS}	600	--	--	V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	$V_{GS(TH)}$	0.9	1.6	2	V
Gate-Source Leakage Current	$V_{GS} = \pm 30\text{V}, V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 100	nA
Drain-Source Leakage Current	$V_{GS} = 0\text{V}, V_{DS} = 600\text{V}$	I_{DSS}	--	--	1	μA
Drain-Source On-State Resistance (Note 3)	$V_{GS} = 10\text{V}, I_D = 0.27\text{A}$	$R_{DS(on)}$	--	11	15	Ω
Dynamic						
Total Gate Charge	$V_{GS} = 10\text{V}, V_{DS} = 480\text{V}, I_D = 0.23$	Q_g	--	7.5	--	nC
Gate-Source Charge		Q_{gs}	--	0.7	--	
Gate-Drain Charge		Q_{gd}	--	4.3	--	
Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 300\text{V}, f = 1.0\text{MHz}$	C_{iss}	--	98	--	pF
Output Capacitance		C_{oss}	--	10	--	
Reverse Transfer Capacitance		C_{rss}	--	8	--	
Switching (Note 4)						
Turn-On Delay Time	$V_{GS} = 10\text{V}, V_{DS} = 300\text{V}, I_D = 0.23\text{A}, R_g = 5\Omega$	$t_{d(on)}$	--	3.6	--	ns
Rise Time		t_r	--	3.9	--	
Turn-Off Delay Time		$t_{d(off)}$	--	15	--	
Fall Time		t_f	--	74	--	
Source-Drain Diode						
Diode Forward Voltage (Note 3)	$V_{GS} = 0\text{V}, I_S = 0.27\text{A}$	V_{SD}	--	0.8	1.5	V
Source Current	Integral reverse diode In the MOSFET	I_S	--	--	0.55	A
Source Current (Pulse)		I_{SM}	--	--	2.2	

Notes:

- Pulse test: Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- Switching time is essentially independent of operating temperature.

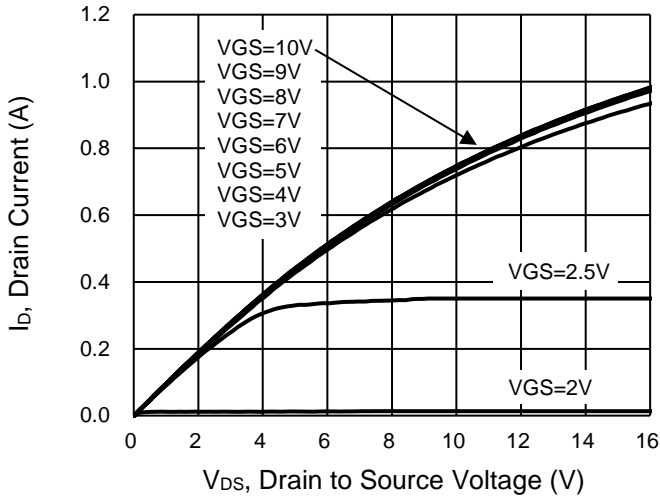
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM1NB60LCW RPG	SOT-223	2,500 pcs / 13" Reel

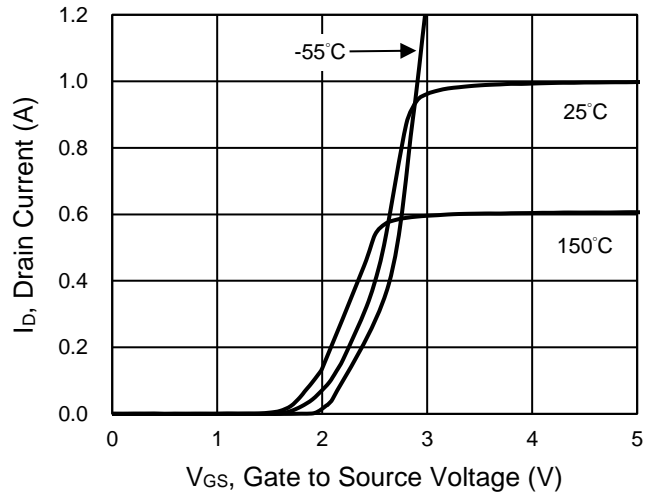
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

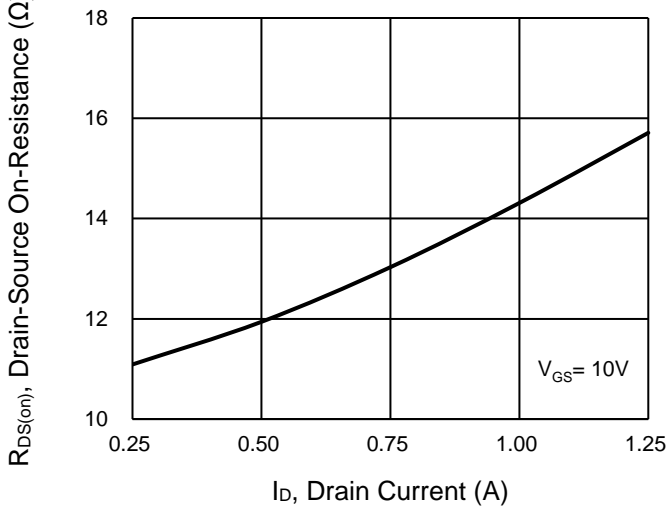
Output Characteristics



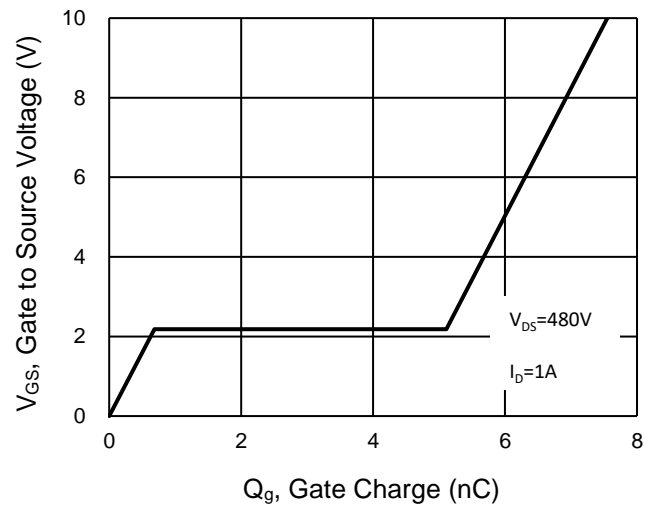
Transfer Characteristics



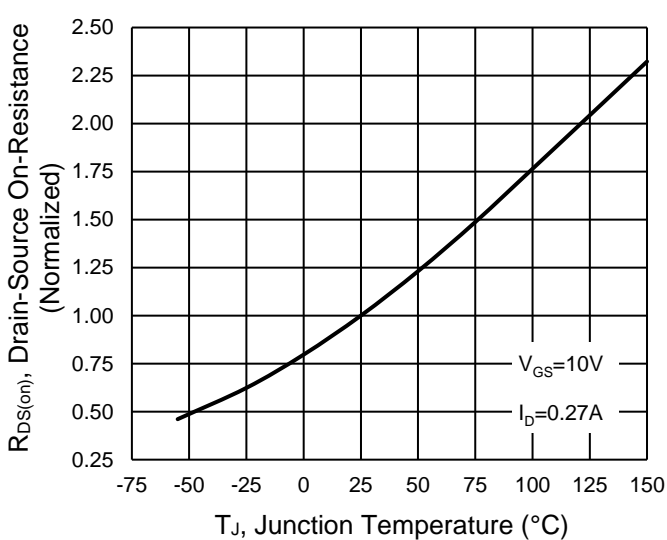
On-Resistance vs. Drain Current



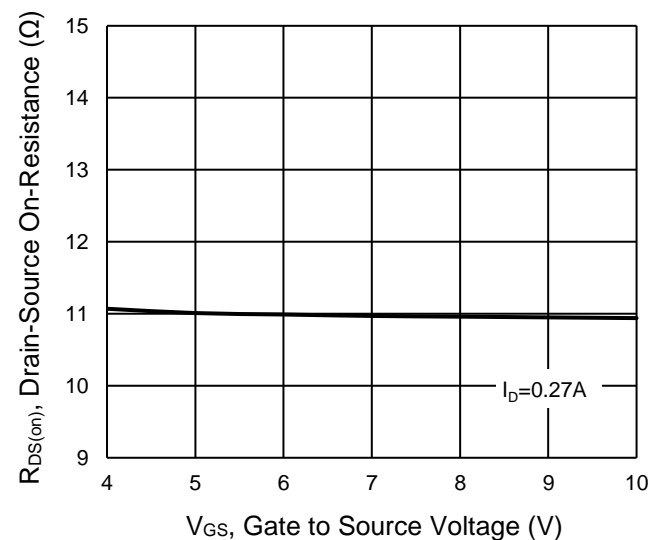
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature

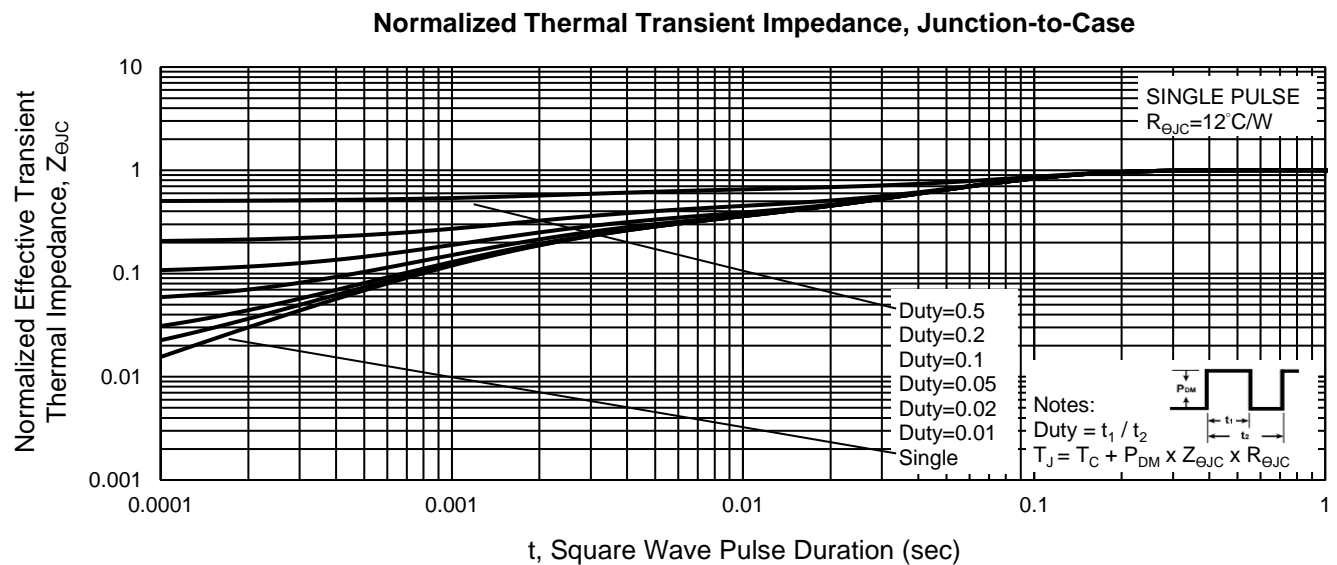
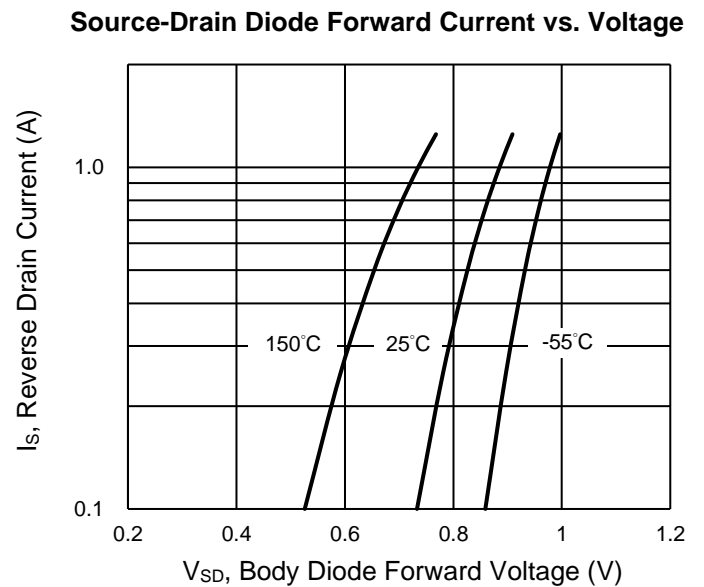
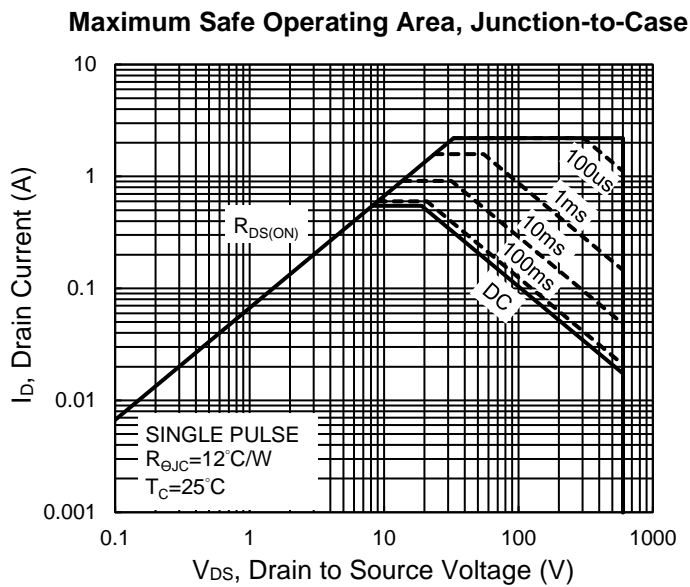
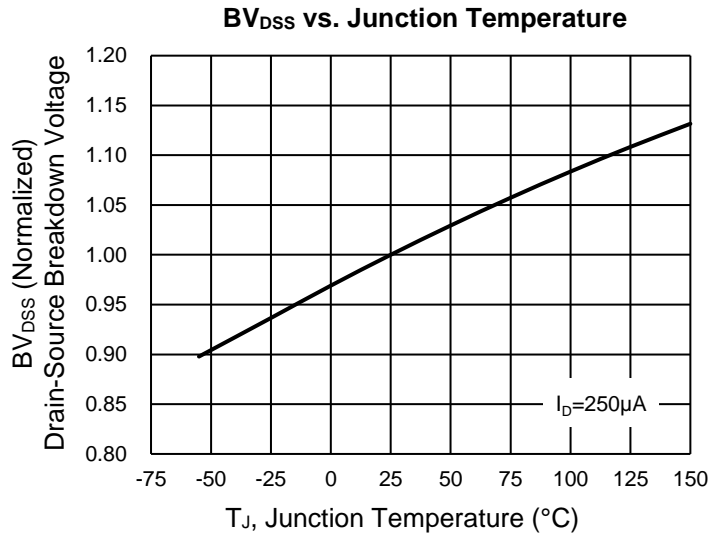
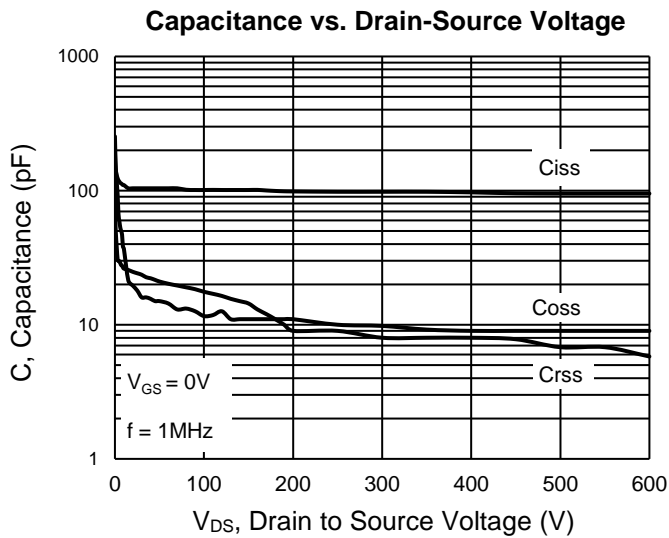


On-Resistance vs. Gate-Source Voltage



CHARACTERISTICS CURVES

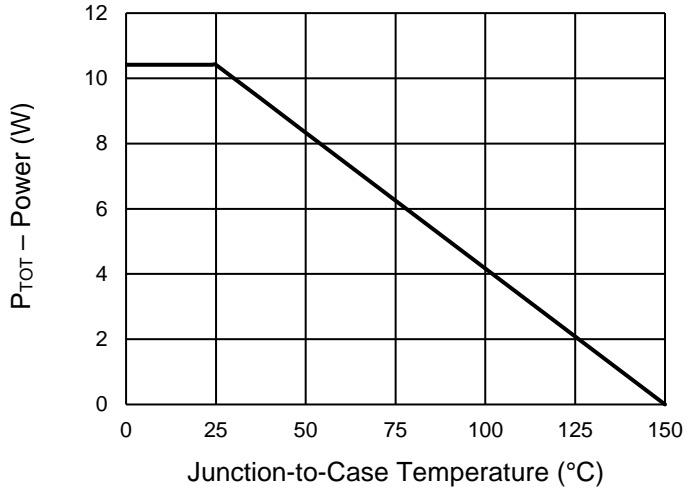
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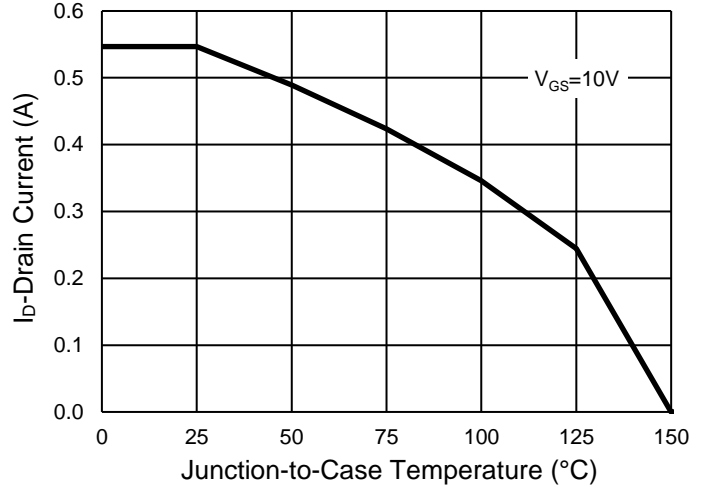
CHARACTERISTICS CURVES

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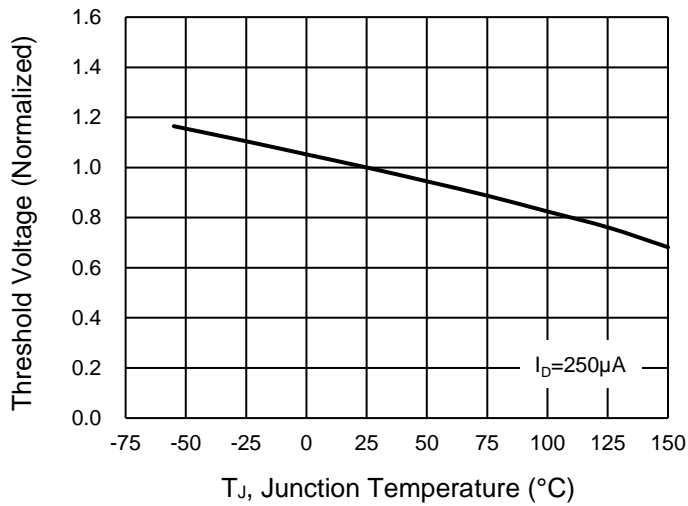
Power Dissipation



Drain Current

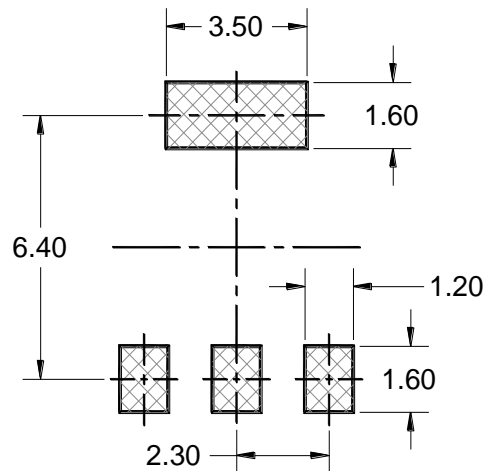
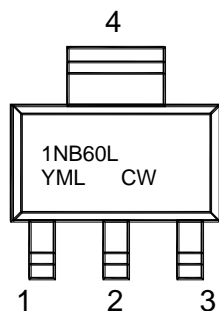
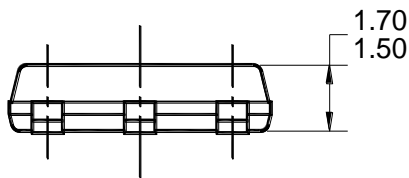
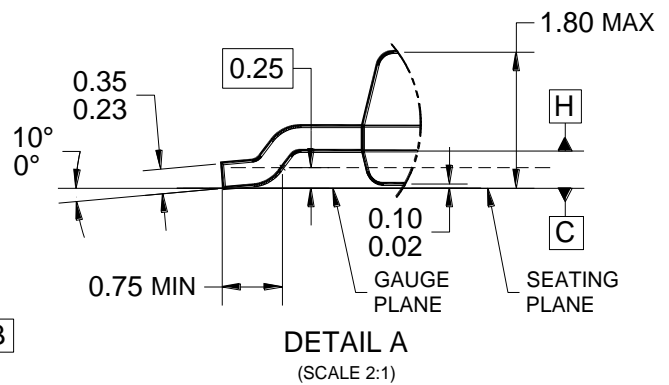
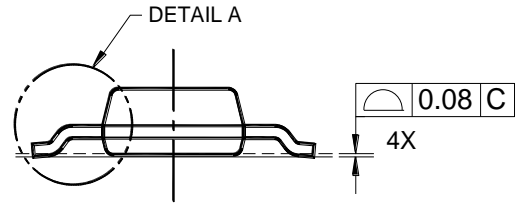
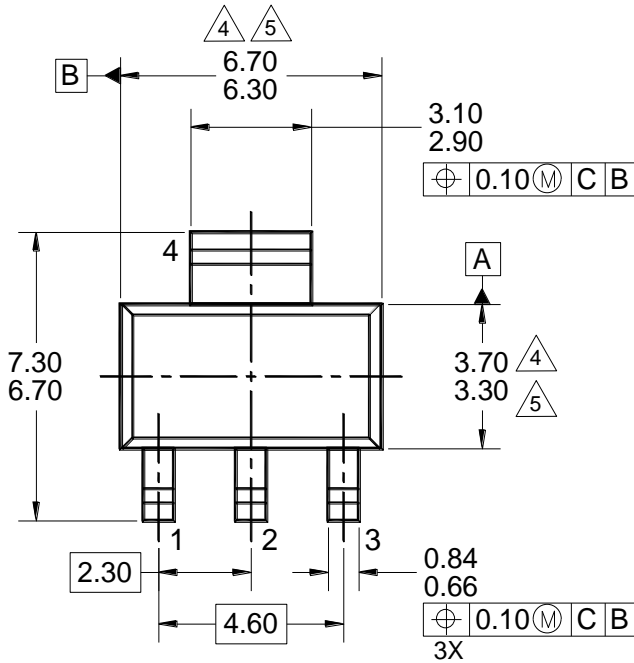


Normalized gate threshold voltage vs Temperature



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

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NOTES: UNLESS OTHERWISE SPECIFIED

- ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- PACKAGE OUTLINE REFERENCE: TO-261, VARIATION AA.
- MOLDED PLASTIC BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH.
- MOLDED PLASTIC BODY LATERAL DIMENSIONS TO BE DETERMINED AT DATUM PLANE H.
- DWG NO. REF: HQ2SD07-SOT223-001 REV A

P/N = MARKING CODE
 Y = YEAR CODE
 M = MONTH CODE FOR HALOGEN FREE PRODUCT
 O = JAN P = FEB Q = MAR R = APRI
 S = MAY T = JUN U = JUL V = AUG
 W = SEP X = OCT Y = NOV Z = DEC
 L = LOT CODE

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